SONY

ICX229AL

Diagonal 4.5mm (Type 1/4) CCD Image Sensor for CCIR B/W Video Cameras

Description

The ICX229AL is an interline CCD solid-state image sensor suitable for CCIR B/W video cameras. Compared with the current product ICX209AL, smear charactristics are improved drastically and power consumption is reduced. High sensitivity and high saturation signal are achieved by Super HAD CCD technology.

This chip features a field period readout system and an electronic shutter with variable charge-storage time.

The package is a 10mm-square 14-pin DIP (Plastic).

Features

- Low smear (-100dB Typ. at F5.6)
- Low power consumption (-38% compared with ICX209AL)
- High sensitivity

(+3dB at F1.2 compared with ICX209AL)

• High saturation signal

• Supply voltage 12V

Horizontal register: 3.3V drive Reset gate: 3.3V drive

• No voltage adjustment

(Reset gate and substrate bias are not adjusted.)

- High resolution, low dark current
- Excellent antiblooming characteristics
- Continuous variable-speed shutter
- Recommended range of exit pupil distance: -20 to -100mm

Device Structure

• Interline CCD image sensor

• Image size: Diagonal 4.5mm (Type 1/4)

Number of effective pixels: 752 (H) × 582 (V) approx. 440K pixels
Total number of pixels: 795 (H) × 596 (V) approx. 470K pixels

• Chip size: 4.34mm (H) \times 3.69mm (V) • Unit cell size: 4.85 μ m (H) \times 4.65 μ m (V)

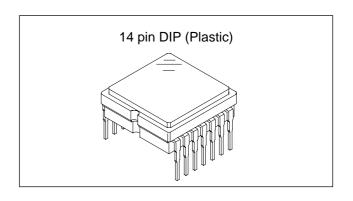
Optical black: Horizontal (H) direction: Front 3 pixels, rear 40 pixels

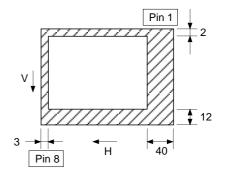
Vertical (V) direction: Front 12 pixels, rear 2 pixels

• Number of dummy bits: Horizontal 22

Vertical 1 (even fields only)

Substrate material: Silicon



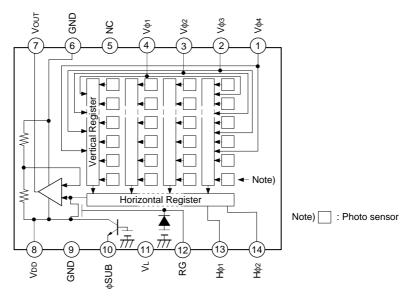


Optical black position (Top View)

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Block Diagram and Pin Configuration

(Top View)



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vф4	Vertical register transfer clock	8	VDD	Supply voltage
2	Vфз	Vertical register transfer clock	9	GND	GND
3	Vф2	Vertical register transfer clock	10	φSUB	Substrate clock
4	Vф1	Vertical register transfer clock	11	VL	Protective transistor bias
5	NC		12	RG	Reset gate clock
6	GND	GND	13	Нф1	Horizontal register transfer clock
7	Vouт	Signal output	14	Нф2	Horizontal register transfer clock

Absolute Maximum Ratings

	Item	Ratings	Unit	Remarks
	Vdd, Vout, RG – фSUB	-32 to +12	V	
Against & CLID	Vφ1, Vφ3 – φSUB	-40 to +15	V	
Against φSUB	Vφ2, Vφ4, VL – φSUB	-40 to +0.3	V	
	Hφ1, Hφ2, GND – φSUB	-32 to +0.3	V	
	Vdd, Vout, RG – GND	-0.3 to +17	V	
Against GND	Vφ1, Vφ2, Vφ3, Vφ4 – GND	-7 to +14	V	
	Hφ1, Hφ2 – GND	-7 to +4.2	V	
Against V	Vφ1, Vφ3 – VL	-0.3 to +21	V	
Against V∟	Vφ2, Vφ4, Hφ1, Hφ2, GND – VL	-0.3 to +12	V	
	Voltage difference between vertical clock input pins	to +12	V	*1
Between input clock pins	Ηφ1 — Ηφ2	−5 to +5	V	
Pillo	Ηφ1, Ηφ2 – Vφ4	-12 to +12	V	
Storage temperature	-30 to +80	°C		
Operating temperature	-10 to +60	°C		

^{*1 +21}V (Max.) when clock width < 10 μ s, clock duty factor < 0.1%.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	VDD	11.64	12.0	12.36	V	
Protective transistor bias	VL	*1				
Substrate clock	φSUB		*2			
Reset gate clock	φRG		*2			

^{*1} VL setting is the VvL voltage of the vertical transfer clock waveform, or the same power supply as the VL power supply for the V driver should be used.

DC Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	IDD		3.5	5.5	mA	

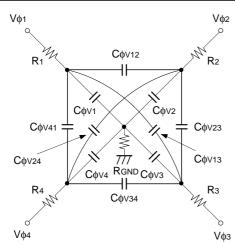
Clock Voltage Conditions

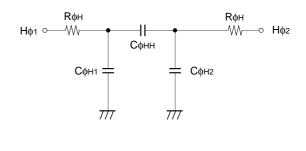
Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	11.64	12.0	12.36	V	1	
	VvH1, VvH2	-0.05	0	0.05	V	2	VvH = (VvH1 + VvH2)/2
	VvH3, VvH4	-0.2	0	0.05	V	2	
	VVL1, VVL2, VVL3, VVL4	-5.5	-5.0	-4.5	V	2	VvL = (VvL3 + VvL4)/2
	Vφv	4.3	5.0	5.55	V	2	$V\phi V = VVHN - VVLN (n = 1 to 4)$
Vertical transfer clock	Vvнз — Vvн	-0.25		0.1	V	2	
voltage	VvH4 – VvH	-0.25		0.1	V	2	
	Vvнн			0.3	V	2	High-level coupling
	VvhL			0.3	V	2	High-level coupling
	Vvlh			0.3	V	2	Low-level coupling
	VVLL			0.3	V	2	Low-level coupling
Horizontal transfer	Vфн	3.0	3.3	3.6	V	3	
clock voltage	VHL	-0.05	0	0.05	V	3	
Reset gate clock	Vørg	3.0	3.3	3.6	V	4	Input through 0.1µF capacitance
voltage	Vrglh – Vrgll			0.4	V	4	Low-level coupling
	VRGL - VRGLm			0.5	V	4	Low-level coupling
Substrate clock voltage	Vфѕив	16.14	17.0	17.86	V	5	

^{*2} Do not apply a DC bias to the substrate clock and reset gate clock pins, because a DC bias is generated within the CCD.

Clock Equivalent Circuit Constant

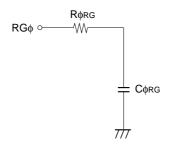
Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Capacitance between vertical transfer	Сф∨1, Сф∨3		1200		pF	
clock and GND	Сфу2, Сфу4		680		pF	
	СфV12, СфV34		220		pF	
Capacitance between vertical transfer	Сф∨23, Сф∨41		150		pF	
clocks	СфV13		82		pF	
	СфV24		75		pF	
Capacitance between horizontal transfer clock and GND	Сфн1, Сфн2		22		pF	
Capacitance between horizontal transfer clocks	Сфнн		36		pF	
Capacitance between reset gate clock and GND	Сфяс		5		pF	
Capacitance between substrate clock and GND	Сфѕив		180		pF	
Vertical transfer clock series resistor	R1, R2, R3, R4		82		Ω	
Vertical transfer clock ground resistor	RGND		15		Ω	
Horizontal transfer clock series resistor	Rфн		12		Ω	
Reset gate clock series resistor	Rørg		51		Ω	





Vertical transfer clock equivalent circuit

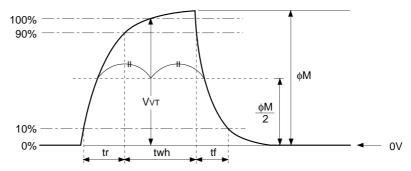
Horizontal transfer clock equivalent circuit



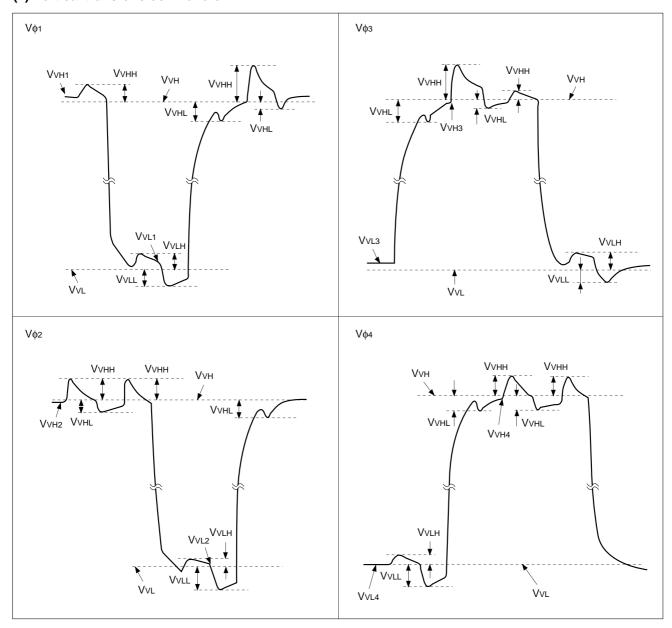
Reset gate clock equivalent circuit

Drive Clock Waveform Conditions

(1) Readout clock waveform



(2) Vertical transfer clock waveform

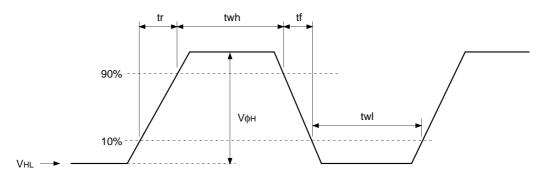


 $V_{VH} = (V_{VH1} + V_{VH2})/2$

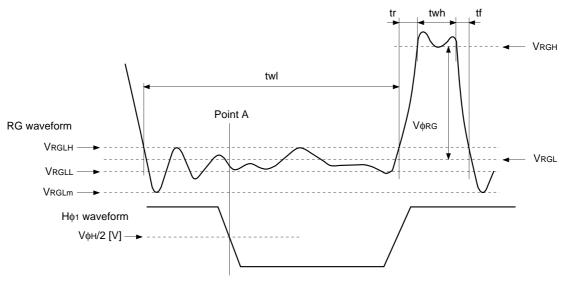
 $V \lor L = (V \lor L3 + V \lor L4)/2$

 $V\phi V = VVHN - VVLN (n = 1 to 4)$

(3) Horizontal transfer clock waveform



(4) Reset gate clock waveform



VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG. In addition, VRGL is the average value of VRGLH and VRGLL.

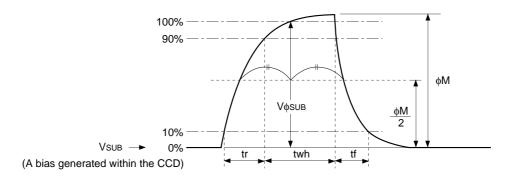
$$V_{RGL} = (V_{RGLH} + V_{RGLL})/2$$

Assuming VRGH is the minimum value during the interval twh, then:

$$V\phi RG = VRGH - VRGL$$

Negative overshoot level during the falling edge of RG is VRGLm.

(5) Substrate clock waveform



Clock Switching Characteristics

	Item	Symbol		twh			twl		tr		tf			Unit	Remarks	
	пеш	Symbol	Min.	Тур.	Max.	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Min.	Тур.	Max.	Offic	Remarks
Rea	dout clock	VT	2.3	2.5						0.5			0.5		μs	During readout
Vert	ical transfer k	Vφ1, Vφ2, Vφ3, Vφ4										15		250	ns	*1
_Ś	During imaging	Нф1	26	28.5		26	28.5			6.5	9.5		6.5	9.5	nc	*2
Horizontal transfer clock		Нф2	26	28.5		26	28.5			6.5	9.5		6.5	9.5	ns	
loriz nsfe	During parallel-serial	Нф1		5.38						0.01			0.01			
tra H	conversion	Нф2					5.38			0.01			0.01		μs	
Res	et gate clock	фRG	11	13			51			3			3		ns	
Sub	strate clock	фѕив	1.5	1.8							0.5			0.5	μs	During drain charge

^{*1} When vertical transfer clock driver CXD1267AN is used.

^{*2} When V ϕ H = 3.0V. tf \geq tr - 2ns, and the cross-point voltage (VcR) for the H ϕ 1 rising side of the H ϕ 1 and H ϕ 2 waveforms must be at least V ϕ H/2 [V].

Item	Symbol		two	Unit	Remarks		
Item	Symbol	Min.	Тур.	Max.	Offic	Remarks	
Horizontal transfer clock	Н ф1, Н ф2	22	26		ns	*3	

^{*3} The overlap period for twh and twl of horizontal transfer clocks $H\phi_1$ and $H\phi_2$ is two.

Image Sensor Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	S	350	440		mV	1	
Saturation signal	Vsat	720			mV	2	Ta = 60°C
Smear	Sm		-100	-90	dB	3	
Video signal shading	CLI			20	%	4	Zone 0 and I
Video signal snading	SH			25	%	4	Zone 0 to II'
Dark signal	Vdt			2	mV	5	Ta = 60°C
Dark signal shading	ΔVdt			1	mV	6	Ta = 60°C
Flicker	F			2	%	7	
Lag	Lag			0.5	%	8	

Zone Definition of Video Signal Shading

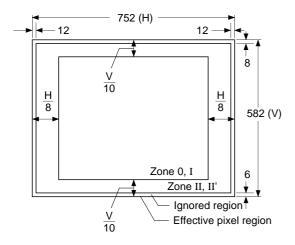


Image Sensor Characteristics Measurement Method

Measurement conditions

1) In the following measurements, the device drive conditions are at the typical values of the bias and clock voltage conditions.

2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black (OB) level is used as the reference for the signal output, and the value measured at point [*A] in the drive circuit example is used.

O Definition of standard imaging conditions

1) Standard imaging condition I:

Use a pattern box (luminance: $706cd/m^2$, color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

3) Standard imaging condition III:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens (exit pupil distance –33mm) with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity

Set to standard imaging condition I. After selecting the electronic shutter mode with a shutter speed of 1/250s, measure the signal output (Vs) at the center of the screen and substitute the value into the following formula.

$$S = Vs \times \frac{250}{50} [mV]$$

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 10 times the intensity with the average value of the signal output, 200mV, measure the minimum value of the signal output.

3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with the average value of the signal output, 200mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (VSm [mV]) of the signal output and substitute the value into the following formula.

Sm =
$$20 \times log \left(\frac{VSm}{200} \times \frac{1}{500} \times \frac{1}{10} \right)$$
 [dB] (1/10V method conversion value)

4. Video signal shading

Set to standard imaging condition III. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 200mV. Then measure the maximum (Vmax [mV]) and minimum (Vmin [mV]) values of the signal output and substitute the values into the following formula.

$$SH = (Vmax - Vmin)/200 \times 100 [\%]$$

5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

$$\Delta Vdt = Vdmax - Vdmin [mV]$$

7. Flicker

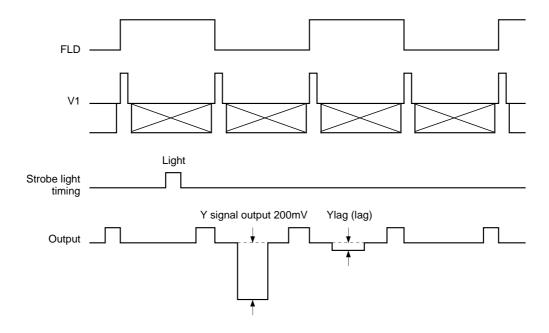
Set to standard imaging condition II. Adjust the luminous intensity so that the average value of the signal output is 200mV, and then measure the difference in the signal level between fields (Δ Vf [mV]). Then substitute the value into the following formula.

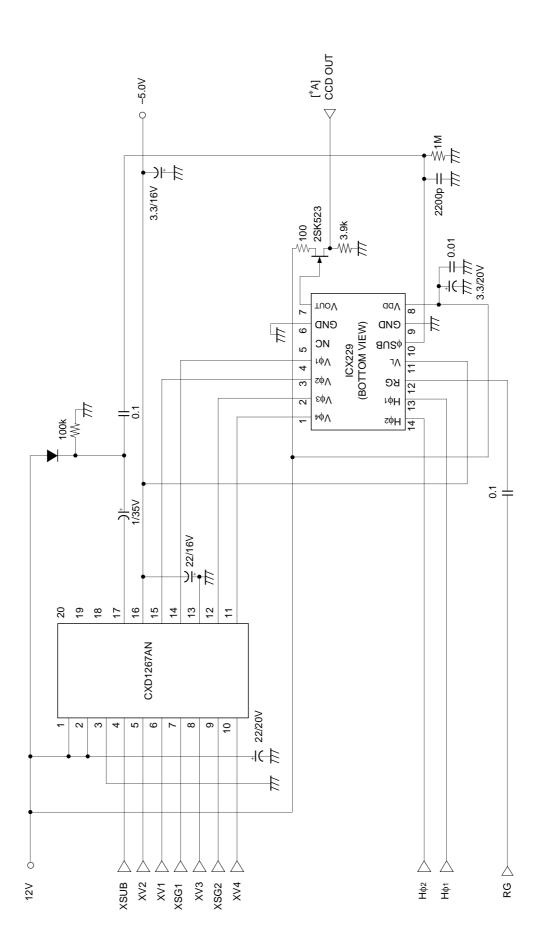
$$F = (\Delta Vf/200) \times 100 [\%]$$

8. Lag

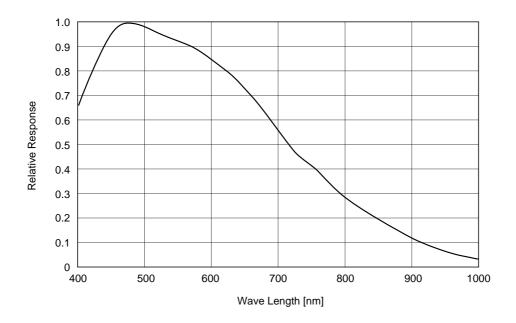
Adjust the signal output value generated by strobe light to 200mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

$$Lag = (Vlag/200) \times 100 [\%]$$

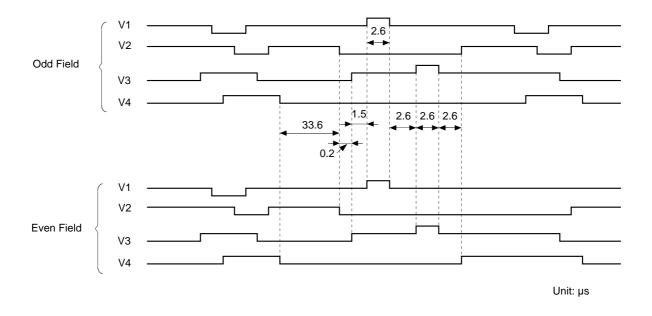


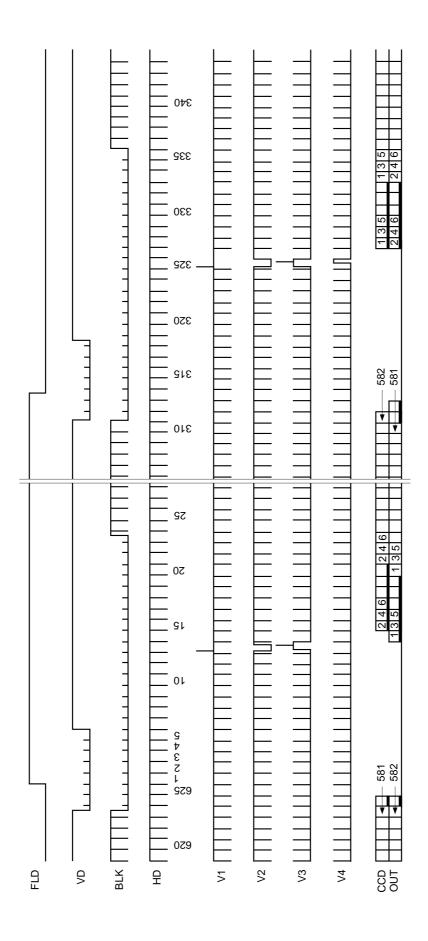


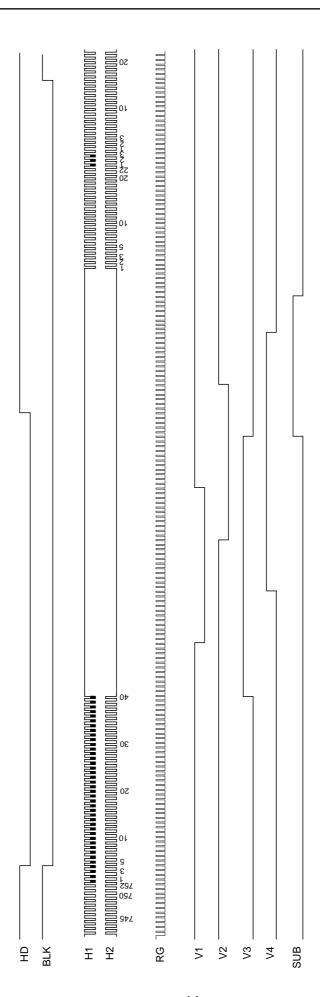
Spectral Sensitivity Characteristics (excludes both lens characteristics and light source characteristics)



Sensor Readout Clock Timing Chart







Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non-chargeable gloves, clothes or material. Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.

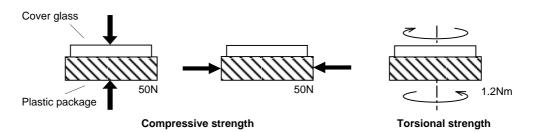
3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

- a) Perform all assembly operations in a clean room (class 1000 or less).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.

4) Installing (attaching)

a) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)

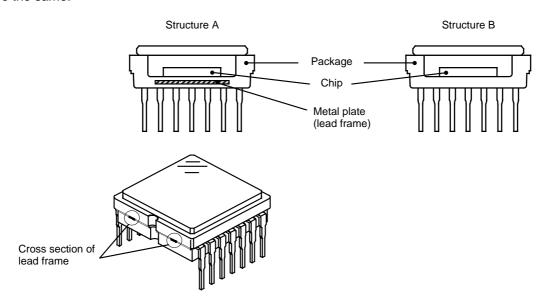


b) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the bottom of the package. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.

- c) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to the other locations as a precaution.
- d) The notch of the package is used for directional index, and that can not be used for reference of fixing. In addition, the cover glass and seal resin may overlap with the notch of the package.
- e) If the lead bend repeatedly and the metal, etc., clash or rub against the package, the dust may be generated by the fragments of resin.
- f) Acrylate anaerobic adhesives are generally used to attach CCD image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives. (reference)

5) Others

- a) Do not expose to strong light (sun rays) for long periods. For continuous using under cruel condition exceeding the normal using condition, consult our company.
- b) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- c) The brown stain may be seen on the bottom or side of the package. But this does not affect the CCD characteristics.
- d) This package has 2 kinds of internal structure. However, their package outline, optical size, and strength are the same.



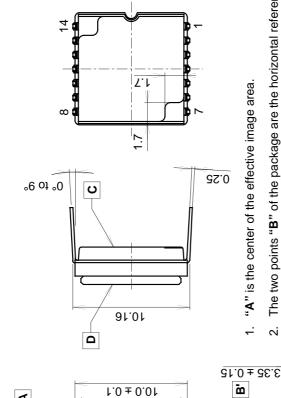
The cross section of lead frame can be seen on the side of the package for structure A.

Unit: mm Package Outline

4

5.0

14 pin DIP (400mil)



- "A" is the center of the effective image area.
- The two points "B" of the package are the horizontal reference. The point "B" of the package is the vertical reference. ď
- The bottom "C" of the package, and the top of the cover glass "D" are the height reference. რ

9.2

0.1

2.5

7.0

1

- The center of the effective image area relative to "**B**" and "**B**" is (H, V) = (5.0, 5.0) \pm 0.15mm. 4.
- The rotation angle of the effective image area relative to H and V is \pm 1°. 5.
- The height from the top of the cover glass "**D**" to the effective image area is 1.94 \pm 0.15mm. The height from the bottom "C" to the effective image area is 1.41 \pm 0.10mm. 6

3.5 ± 0.3

 (\mathbf{Z})

0.3

 \oplus

0.3 72.1

1.27

- The tilt of the effective image area relative to the bottom " \mathbf{C} " is less than 25 μ m. The tilt of the effective image area relative to the top " \mathbf{D} " of the cover glass is less than 25 μ m. ۲.
- The thickness of the cover glass is 0.75mm, and the refractive index is 1.5. ω.
- The notch of the package is used only for directional index, that must not be used for reference 6

PACKAGE STRUCTURE

Plastic	GOLD PLATING	42 ALLOY	0.60g	AS-D3 -01(E)
PACKAGE MATERIAL	LEAD TREATMENT	LEAD MATERIAL	PACKAGE MASS	DRAWING NUMBER

4	10.0 ± 0.1
0.8	
3.5 3.7	9.0
	0:

1.0 ± 0.01

6;8